

AMENDMENTS TO THE CLAIMS

Following is a listing of all claims in the present application, which listing supersedes all previously presented claims:

Listing of Claims:

1. (Currently Amended) A method of forming a via hole through a glass wafer, comprising:

depositing a first material layer on front and rear surfaces ~~an outer surface~~ of the glass wafer;

depositing a second material layer on the first material layer;

forming a via pattern in the second material layer;

performing a first etching using the via pattern to form a hole passing through the first material layer on the front surface of the glass wafer and a preliminary via hole in the glass wafer, wherein the preliminary via hole does not pass completely through the glass wafer;

eliminating the second material layer;

performing a second etching in which the preliminary via hole is etched to form a blind via hole having a smooth surface and extending through the glass wafer but not through the first material layer on the rear surface of the glass wafer, such that the first material layer on the rear surface of the glass wafer is exposed through the blind via hole;

and

eliminating the first material layer, such that the blind via hole is transformed into a through hole.

2. (Previously Presented) The method as claimed in claim 1, wherein the first material layer is formed of polysilicon.
3. (Original) The method as claimed in claim 1, wherein the first etching is performed by sandblasting.
4. (Original) The method as claimed in claim 1, wherein the first etching is performed by a device selected from the group consisting of: an ultrasonic wave, a drill, and a laser beam.
5. (Currently Amended) The method as claimed in claim 1, wherein, during the first etching, the glass wafer is etched to a sufficient depth so that the preliminary via hole has a bottom adjacent to the rear surface ~~another side~~ of the glass wafer.
6. (Previously Presented) The method as claimed in claim 1, wherein forming a via pattern in the second material layer further comprises:

 exposing and developing the second material to form the via pattern, wherein the second material is a film resistor.
7. (Original) The method as claimed in claim 6, wherein the film resistor comprises a material having a large resistance to sandblast etching to permit the film resistor to function as a protection film during subsequent sandblasting of the glass wafer.

8. (Original) The method as claimed in claim 1, wherein the second etching is a wet etching.
9. (Original) The method as claimed in claim 8, wherein the wet etching uses a hydrofluoric acid (HF) solution.
10. (Previously Presented) The method as claimed in claim 1, wherein the first material layer has a selection ratio higher than that of the glass wafer.